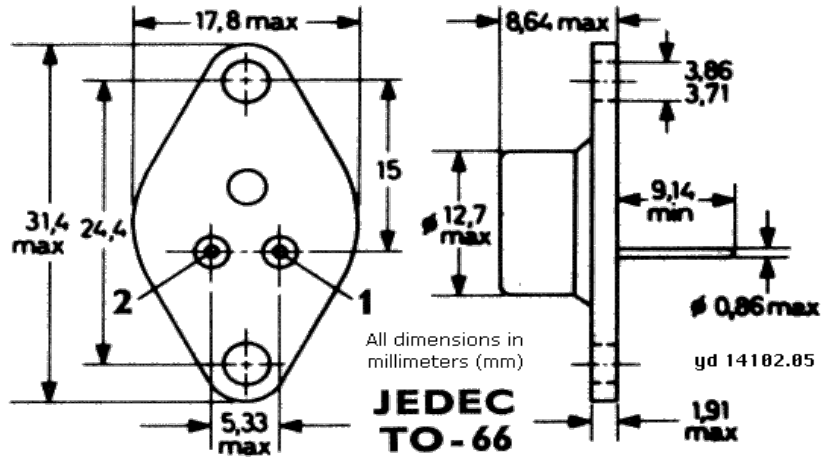


BU406/406H/408

NPN EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE SWITCHING USE IN HORIZONTAL DEFLECTION OUTPUT STAGE



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	400	V
Collector-Emitter Voltage	V _{CE0}	200	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Current (DC)	I _C	7	A
Collector Peak Current	I _{CM}	10	A
Base Current (DC)	I _B	4	A
Collector Dissipation (T _c =25 °C)	P _C	60	W
Junction Temperature	T _j	50	°C
Storage Temperature	T _{stg}	-65-150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current (V _{BE} =0)	I _{CES}	V _{CE} =400V, V _{EB} =0			5	mA
		V _{CE} =250V, V _{EB} =0			100	µA
		V _{CE} =250V, V _{EB} =0			1	mA
Emitter Cutoff Current (I _C =0)	I _{EBO}	V _{CE} =250V, V _{EB} =0			1	mA
Collector Emitter Saturation Voltage : BU406 : BU406H : BU408	V _{CE(sat)}	T _c =150			1	V
		V _{EB} =6V, I _C =0			1	V
		I _C =5A, I _B =0.5A			1.2	V
		I _C =5A, I _B =0.8A			1.2	V
Base Emitter Saturation Voltage : BU406 : BU406H : BU408	V _{BE(sat)}	I _C =6A, I _B =1.2A			1.5	V
		I _C =5A, I _B =0.5A	1	0		MHZ
		I _C =5A, I _B =0.8A			0.75	µS
Current Gain Bandwidth Product	f _T	I _C =5A, I _B =0.5A			0.4	µS
		I _C =5A, I _B =0.8A			0.4	µS
		I _C =6A, I _B =1.2A			0.4	µS
		V _{CE} =10V, I _C =500mA			0.4	µS
Turn Off Time :	t _{off}	I _C =5A, I _B =0.5A				
		I _C =5A, I _B =0.8A				
		I _C =6A, I _B =1.2A				